

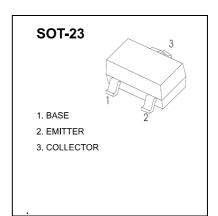
### **SOT-23 PNP Plastic-Encapsulate Transistors**

#### **FEATURE**

- Ldeally suited for automatic insertion
- Epitaxial planar die construction
- Complementary NPN type available(BC817)

#### MAXIMUM RATINGS (T<sub>3</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	<b>-</b> 50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	<del>-</del> 45	V
V <sub>EBO</sub>	Emitter-Base Voltage	<b>-</b> 5	V
Ic	Collector Current	<b>-</b> 500	mA
Pc	Collector Power Dissipation	300	mW
R <sub>OJA</sub>	Thermal Resistance From Junction To Ambient	417	°C/W
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	<b>-</b> 55~+150	°C



**ELECTRICAL CHARACTERISTICS (T**a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> =0	-50		V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	<b>-</b> 45		V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -1μΑ, I <sub>C</sub> =0	<b>-</b> 5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -45V, I <sub>E</sub> =0		-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4 V, I <sub>C</sub> =0		-0.1	μА
DC current gain	hFE(1)	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA	100	600	
-	hFE(2)	V <sub>CE</sub> = -1V, I <sub>C</sub> = -500mA	40		
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =-500mA, I <sub>B</sub> = -50mA		-0.7	٧
Base-emitter saturation voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA		-1.2	V
Transition frequency	f⊤	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA f=100MHz	100		MHz

#### CLASSIFICATION OF hee (1)

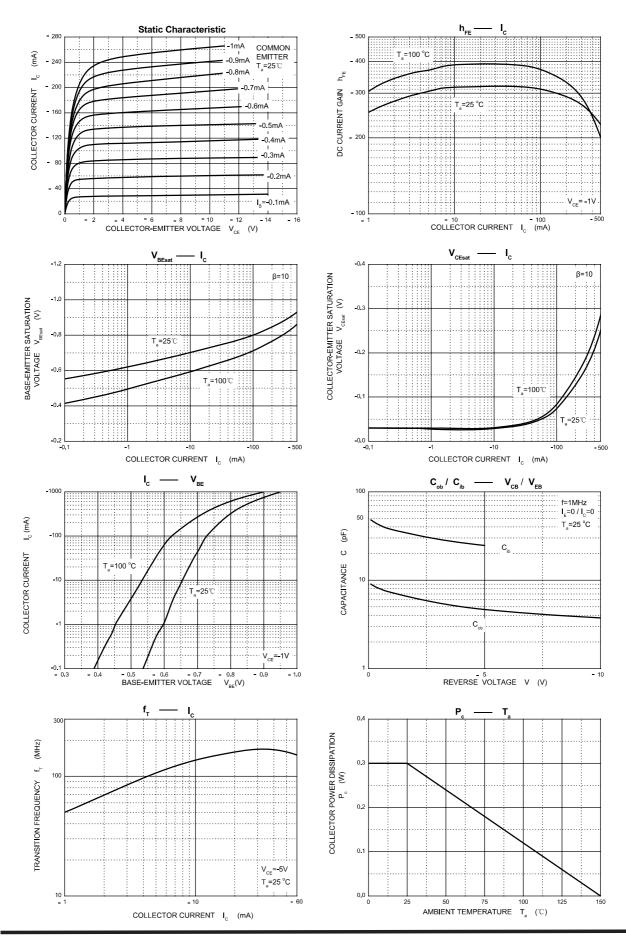
Rank	BC807-16	BC807-25	BC807-40
Range	100-250	160-400	250-600
Marking	5A	5B	5C



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AS-3140050	2003/03/08	2012/05/16	D	3



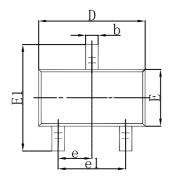
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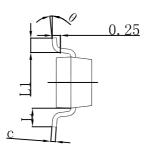


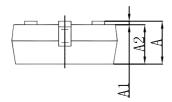


### **SOT-23 PNP Plastic-Encapsulate Transistors**

# **SOT-23 Package Outline Dimensions**

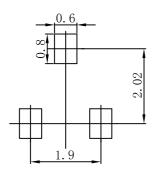






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	6°	

# **SOT-23 Suggested Pad Layout**



### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

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